

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2002-006503

(43)Date of publication of application : 09.01.2002

(51)Int.Cl.

G03F 7/039
G08K 5/13
G08K 5/42
G08L101/12
G03F 7/004
G03F 7/38
H01L 21/027

(21)Application number : 2001-114812

(71)Applicant : SHIN ETSU CHEM CO LTD

(22)Date of filing : 13.04.2001

(72)Inventor : KATO HIDETO
NISHIKAWA KAZUHIRO
HIRANO SADANORI
TAKEMURA KATSUYA

(30)Priority

Priority number : 2000115737 Priority date : 17.04.2000 Priority country : JP

(54) RESIST MATERIAL AND PATTERN-FORMING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a resist material capable of forming a pattern, having high resolution and high sensitivity and excellent in plating resistance by exposure, particularly with UV exposure with ≥ 300 nm wavelength, and to provide a pattern forming method.

SOLUTION: The resist material using UV exposure with ≥ 300 nm wavelength as a light source for exposure contains (A) an alkali-insoluble or slightly alkali-soluble high molecular compound, having an acidic functional group protected by an acid labile group and convertible to an alkali-soluble compound when the acid labile group is released, (B) an acid-generating agent and (C) a compound having a 1,2-naphthoquinonediazidosulfonyl group in its molecule.

LEGAL STATUS

[Date of request for examination] 22.04.2004

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision
of rejection]

[Date of extinction of right]